

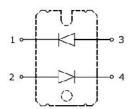
Anti-parallel Fast Recovery 2X150A, 400V Epitaxial Diodes, in Isolated SOT227 Package

APPLICATIONS

- Switch mode power supplies (SMPS) rectifiers
- Uninterruptible power supplies (UPS)
- > Ultrasonic cleaners and welders
- Inductive heating and melting
- Ultrasonic cleaners and welders
- > Power factor correction (PFC) circuits
- > Inversion welder
- Converter and chopper

FEATURES

- Ultrafast recovery time
- Low forward voltage
- High surge current capability
- Low leakage current
- Pb-free finished; RoHS compliant





MAXIMUM RATINGS (per Diode)

Parameter	Symbol	Value	Units	
Repetitive peak reverse voltage	V_{RRM}	400	V	
Average forward current, per Diode T _C = 90 °C	l _{F(AV)}	150	A	
Average forward current, per Device T _C = 90 °C		300		
Maximum repetitive forward current, square wave, 20kHz	I _{FRM}	240		
Surge non-repetitive forward current T_c = 25°C, t_p = 10 ms, 50Hz, Sine	I _{FSM}	1200		
Operating junction and storage temperature	T _j , T _{stg}	-55 +175	°C	

Thermal and Isolation Characteristics

Parameter	Symbol	Max. Value	Units
Characteristics			
Thermal resistance, junction to case, per Diode	R _{thJC}	0.45	°C/W
Isolation voltage, RMS (measured between terminals and mounting base, 50-60 Hz, for 3 seconds)	V _{iso}	3000	V



Electrical Characteristics, at T_i = 25°C, unless otherwise specified

Parameter	Sumala al	Value			IIm!I
	Symbol	Min.	Тур.	Max.	Unit
Static Characteristics					
Breakdown voltage $I_R = 200 \mu A$, $T_i = 25 ^{\circ} C$	V_{Br}	400	-	-	٧
Reverse leakage current $V_R = 400V$, T_i =25°C		-	-	100	μA
Reverse leakage current $V_R = 400V$, $T_i = 150$ °C	l _R	-	-	4	mA
Forward voltage drop I _F = 150A, T _j = 25 °C I _F = 150A, T _j = 150 °C	V _F		1.18 1.15	1.42 1.38	٧

Electrical Characteristics, at Tj = 25°C, unless otherwise specified

Parameter	Comple of	Value			1124
	Symbol	Min.	Тур.	Max.	Unit
Dynamic Characteristics					
Reverse recovery time $V_R = 30V$, $I_F = 1A$, $di_F/dt = -200A/\mu s$, $T_j=25$ °C		-	50	-	
Reverse recovery time $V_R = 200V$, $I_F = 150A$, $di_F/dt = -200A/\mu s$, $T_i = 25$ °C	† _{rr}	_	125	_	ns
$V_R = 200V$, $I_F = 150A$, $di_F/dt = -200A/\mu s$, $T_{j=125} \circ C$		1	285	-	
Reverse recovery charge V _R = 200V, I _F = 150A, di _F /dt = -200A/µs, T _i =25°C V _R = 200V, I _F = 150A, di _F /dt = -200A/µs, T _i =125°C	Qrr	-	514 3840	-	nC
Maximum reverse recoverycurrent V _R = 200V, I _F = 150A, di _F /dt = -200A/µs, T _i =25°C V _R = 200V, I _F = 150A, di _F /dt = -200A/µs, T _i =125°C	Irm	-	8 25	-	Α

Figure 1 – Typical Forward Voltage Drop vs Forward
Current

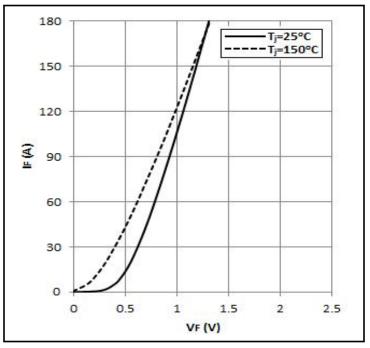
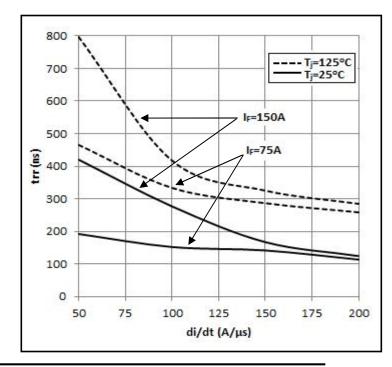


Figure 2 – Reverse recovery time vs. di_F/dt



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Figure 3 – Reverse recovery charge vs. di_F/dt

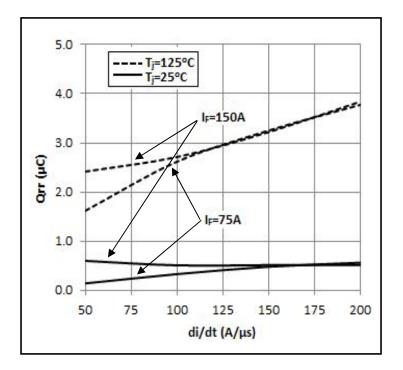


Figure 4 – Maximum reverse recovery current vs. di_F/dt

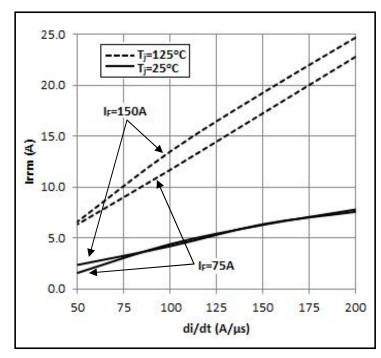
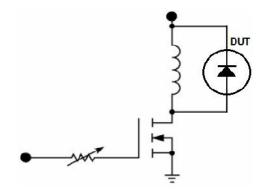
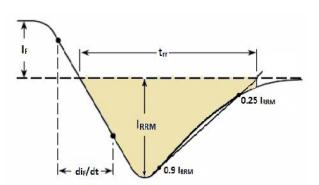


Figure 5 – Diode Reverse Recovery Test Circuit and Waveform



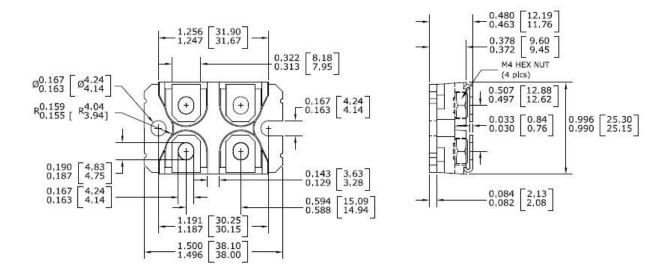


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Package Outline Drawing



Disclaimer

These specifications may not be considered as a guarantee of components characteristics. Components have to be tested depending on intended application as adjustments may be necessary. The use of **iQXPRZ Power Inc.** components in life support appliances and systems are subject to written approval of **iQXPRZ Power Inc.**

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